

# MC74HC540A

## Octal 3-State Inverting Buffer/Line Driver/Line Receiver

### High-Performance Silicon-Gate CMOS

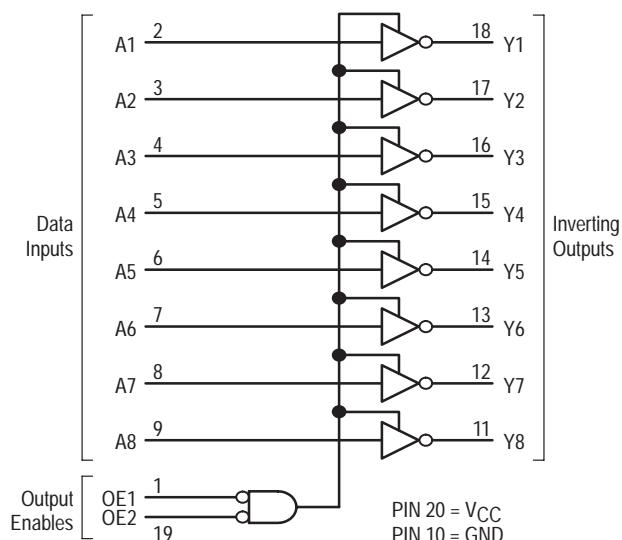
The MC74HC540A is identical in pinout to the LS540. The device inputs are compatible with Standard CMOS outputs. External pullup resistors make them compatible with LSTTL outputs.

The HC540A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC540A is similar in function to the HC541A, which has non-inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1 $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 124 FETs or 31 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

Inputs		Output Y
OE1	OE2	
L	L	L
L	L	H
H	X	X
X	H	X

Z = High Impedance

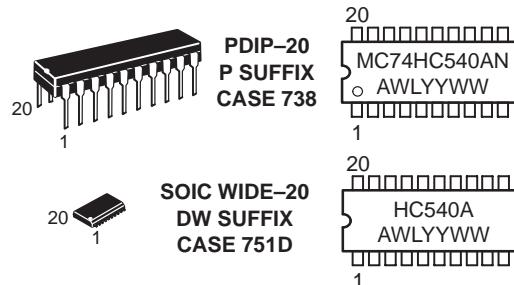
X = Don't Care



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#### MARKING DIAGRAMS



A = Assembly Location

WL = Wafer Lot

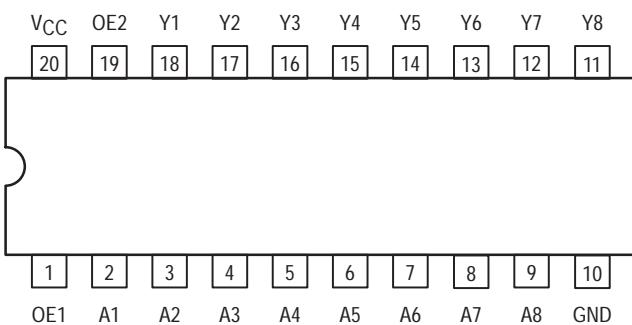
YY = Year

WW = Work Week

#### ORDERING INFORMATION

Device	Package	Shipping
MC74HC540AN	PDIP-20	1440 / Box
MC74HC540ADW	SOIC-WIDE	38 / Rail
MC74HC540ADWR2	SOIC-WIDE	1000 / Reel

#### Pinout: 20-Lead Packages (Top View)



# MC74HC540A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	–0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	–0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	–0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T <sub>stg</sub>	Storage Temperature Range	–65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP or SOIC Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: –10 mW/°C from 65° to 125°C

SOIC Package: –7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature Range, All Package Types	–55	+125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 1)	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	0 0 0	1000 500 400	ns

## DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> V	Guaranteed Limit			Unit
				–55 to 25°C	≤85°C	≤125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1V  I <sub>out</sub>   ≤ 20µA	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = V <sub>CC</sub> – 0.1V  I <sub>out</sub>   ≤ 20µA	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IL</sub>  I <sub>out</sub>   ≤ 20µA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V <sub>in</sub> = V <sub>IL</sub>  I <sub>out</sub>   ≤ 3.6mA  I <sub>out</sub>   ≤ 6.0mA  I <sub>out</sub>   ≤ 7.8mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub>  I <sub>out</sub>   ≤ 20µA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V <sub>in</sub> = V <sub>IH</sub>  I <sub>out</sub>   ≤ 3.6mA  I <sub>out</sub>   ≤ 6.0mA  I <sub>out</sub>   ≤ 7.8mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	µA

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## DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> V	Guaranteed Limit			Unit
				-55 to 25°C	≤85°C	≤125°C	
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High Impedance State V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	6.0	±0.5	±5.0	±10.0	µA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0µA	6.0	4	40	160	µA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## AC CHARACTERISTICS (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6 ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit	
			-55 to 25°C	≤85°C	≤125°C		
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns	
t <sub>PZL</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns	
t <sub>PZH</sub> , t <sub>PZL</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns	
C <sub>in</sub>	Maximum Input Capacitance			10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High Impedance State)			15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*	Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V		pF
		35		

\* Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## SWITCHING WAVEFORMS

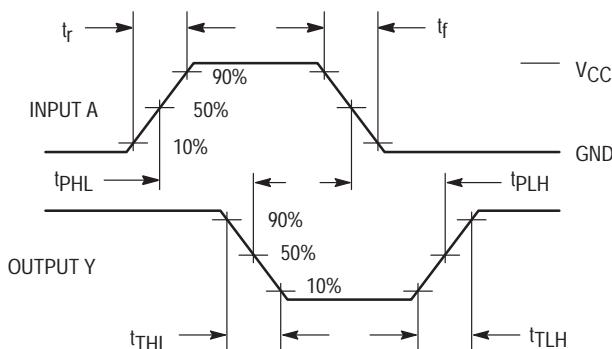


Figure 1.

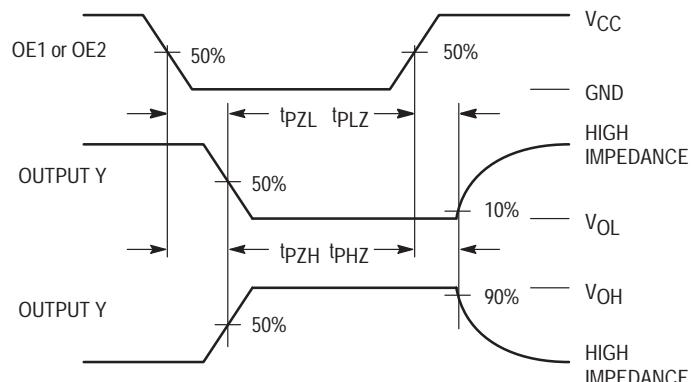
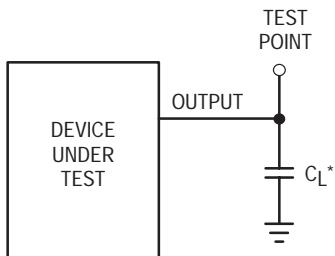


Figure 2.

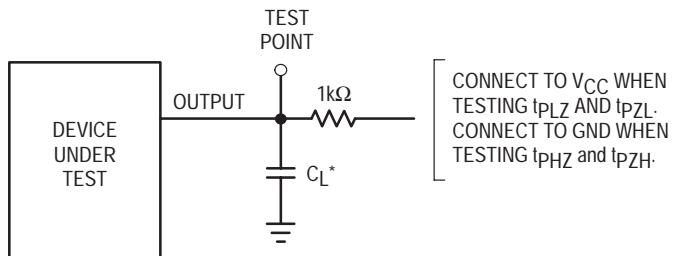
MC74HC540A

## TEST CIRCUITS



\*Includes all probe and jig capacitance

**Figure 3.**



\*Includes all probe and jig capacitance

**Figure 4.**

## PIN DESCRIPTIONS

## INPUTS

**A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)**— Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

## CONTROLS

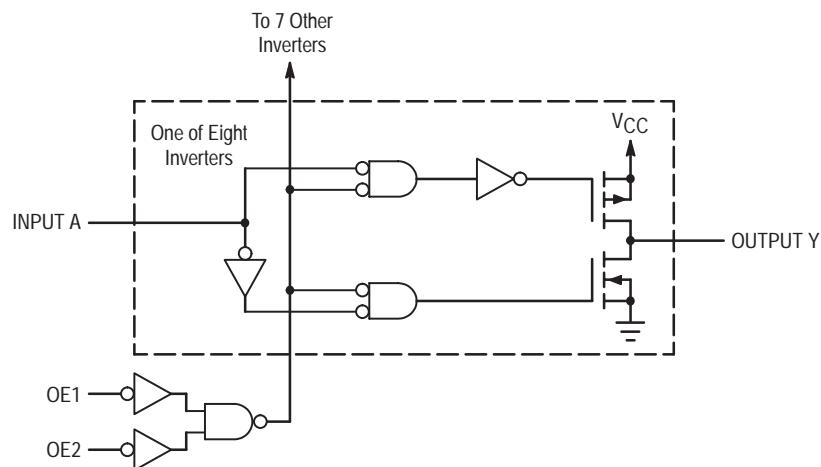
**OE1, OE2 (PINS 1, 19)** — Output enables (active-low). When a low voltage is applied to both of these pins, the

outputs are enabled and the device functions as an inverter. When a high voltage is applied to either input, the outputs assume the high impedance state.

## OUTPUTS

**Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)** — Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high-impedance outputs.

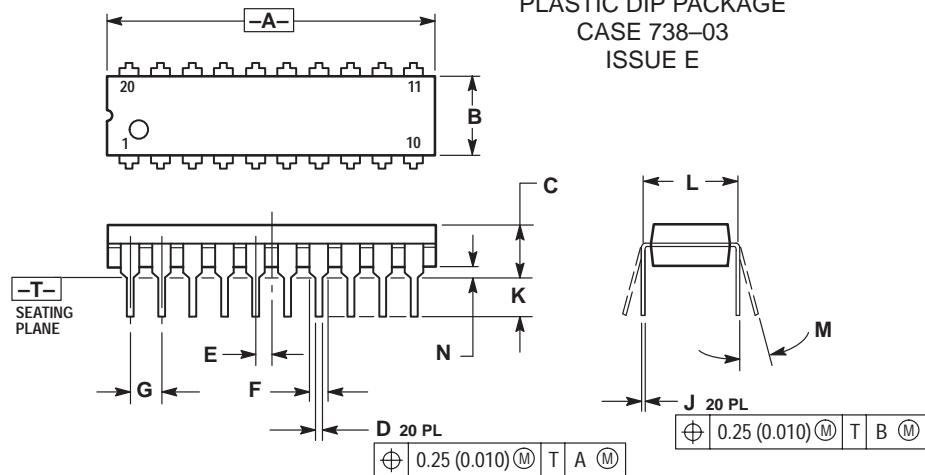
## LOGIC DETAIL



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## PACKAGE DIMENSIONS

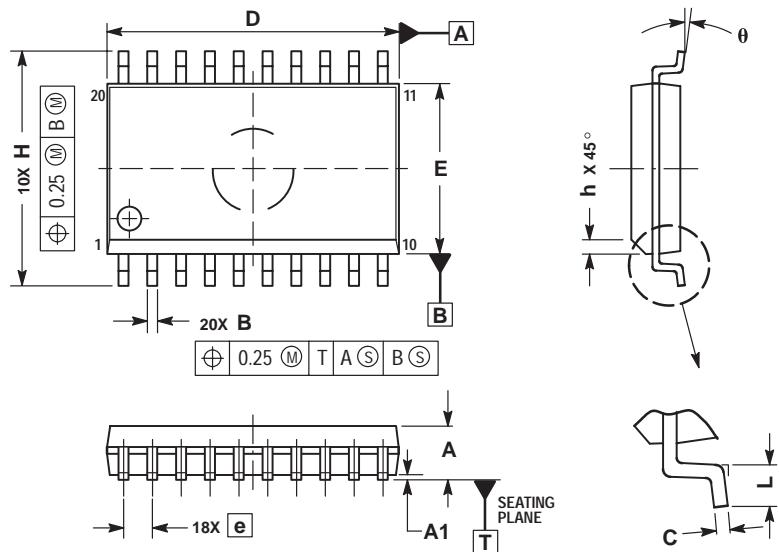
**PDIP-20  
N SUFFIX  
PLASTIC DIP PACKAGE  
CASE 738-03  
ISSUE E**



NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.  
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.  
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

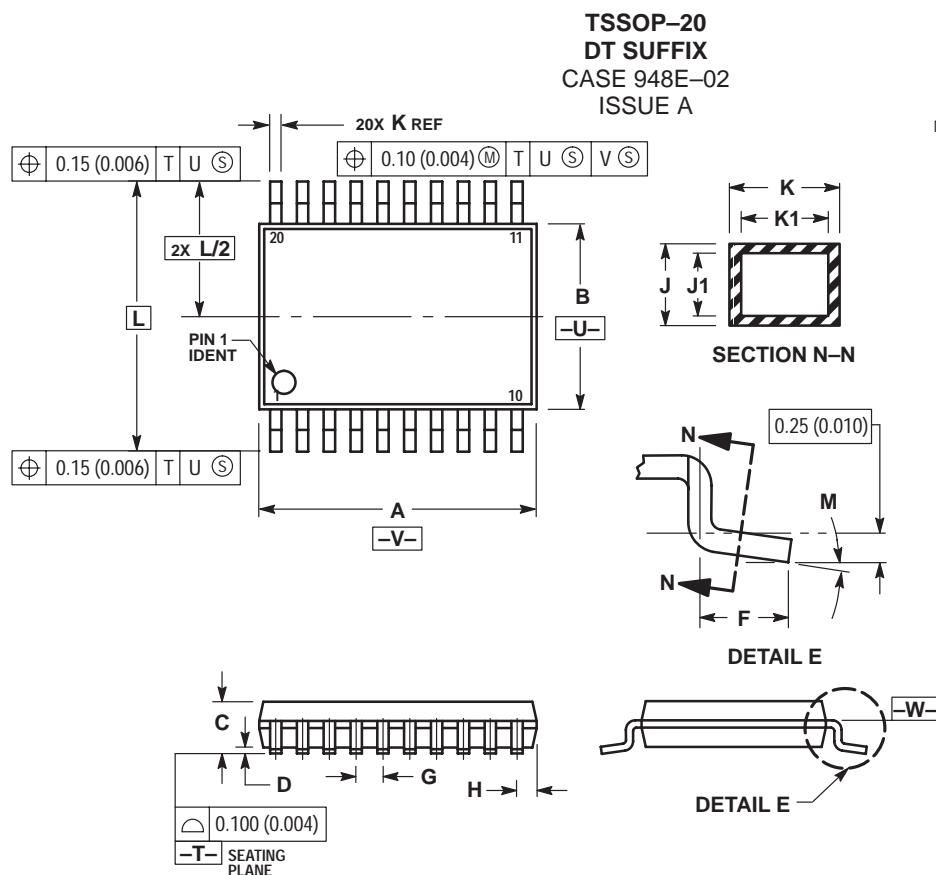
**SO-20  
DW SUFFIX  
CASE 751D-05  
ISSUE F**



NOTES:  
 1. DIMENSIONS ARE IN MILLIMETERS.  
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.  
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.  
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.  
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
$\theta$	0°	7°

## PACKAGE DIMENSIONS



## NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE **-W-**.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

## **Notes**

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